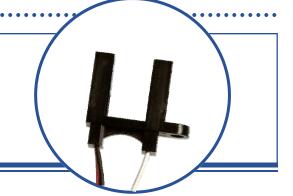


Features:

- 24" (610 mm) long 26 gauge wired assembly
- Non-contact infrared switch
- · Opaque plastic housing
- 0.375" (9.5 mm) slot width
- 0.595" (15.1 mm) slot depth

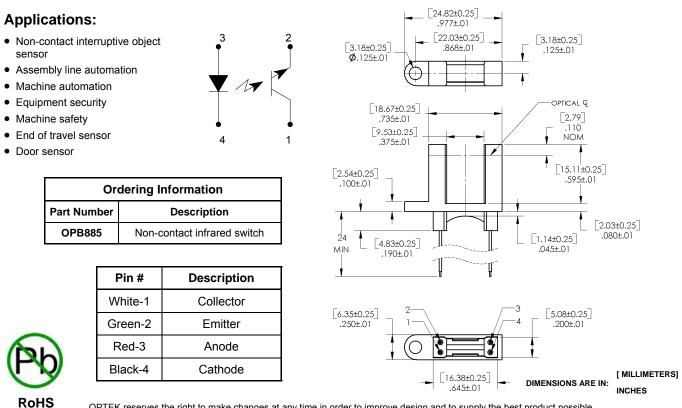


Description:

OPB885 uses an Infrared LED and a phototransistor in a slotted switch configuration. The assembly has 24" (610mm) 26 AWG wires on each terminal and uses an opaque housing to reduce the sensor's ambient light sensitivity. Each discrete has an 0.050" (1.27 mm) aperture that focuses the switching sensitivity and limits ambient light absorption by the phototransistor. The housing is made from an opague plastic with IR transmissive plastic in the front of each aperture to provide dust protection.

In the normal unobstructed slot, infrared light from the LED, radiates the phototransistor and becomes forward biased and is considered to be in the "on" state, providing an I_{C(ON)} current that is proportional to the light striking the phototransistor. As the light is blocked by using an opaque object that blocks the infrared light from the LED to the phototransistor, the phototransistor turns "off," minimizing the $I_{C(ON)}$ current and thus allowing the electrical state to be considered switched.

Custom electrical, wire and cabling and connectors are available. Contact your local representative or OPTEK for more information.



OPTEK reserves the right to make changes at any time in order to improve design and to supply the best product possible



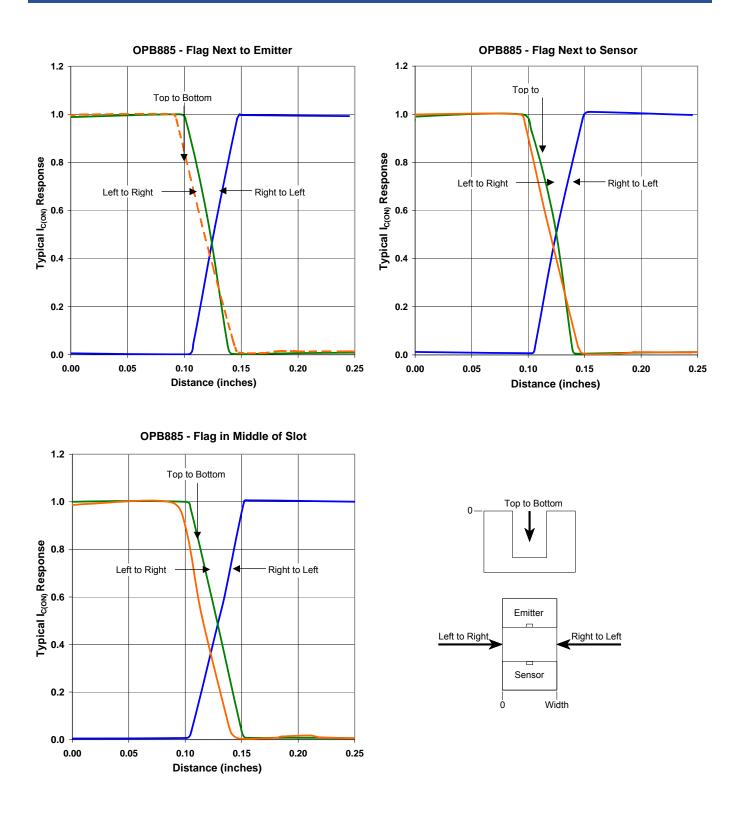
Storage Temperature							-40° C to +100° C
Operating Temperature							-40° C to +85° C
Lead Soldering Temperature (1/16 inch (1.6mm) from the case for 5 sec. with soldering iron) ⁽²⁾							260° C
.ED							
Forward Current							50 mA
Peak Forward Current (2 µs pulse width, 0.1% duty cycle)							1 A
Reverse DC Voltage							3 V
Power Dissipation							100 mW
Output Ph	ototransistor						
Collector-Emitter Voltage							30 V
Collector DC Current							50 mA
Power Dissipation							100 mW
Electrica	al Characteristics (T _A = 25°C unles	ss othe	erwise r	noted)			
SYMBOL	PARAMETER	MIN	TYP	MAX	UNITS	TEST CONDITIONS	
nput Diod	le (see OP345 for additional information)			•			
VF	Forward Voltage	-	-	1.7	V	I _F = 20 mA	
I _R	Reverse Current	-	-	100	μA	V _R = 3 V	
Output Ph	ototransistor (see OP555 for additional	informa	ition)				
BV_{CEO}	Collector-Emitter Breakdown Voltage	30	-	-	V	I _C = 1 mA	
I _{CEO}	Collector-Emitter Dark Current	-	-	100	nA	V _{CE} = 10 V	
Combined	I					•	
V _{CE(SAT)}	Collector-Emitter Saturation Voltage	-	-	0.6	V	$I_{\rm C}$ = 1 mA, $I_{\rm F}$ = 20 mA	
	On-State Collector Current	1.3		8	mA	V _{CE} = 5 V, I _F = 20 mA	

(1) All parameters tested using pulse technique.
(2) RMA flux is recommended. Duration can be extended to 10 seconds maximum when flow soldering.

(3) Methanol or isopropanol are recommended as cleaning agents. The plastic housing is soluble in chlorinated hydrocarbons and keytones.

Slotted Switch OPB885Z





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